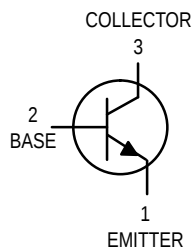
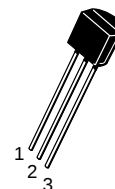


Amplifier Transistors

NPN Silicon



2N2222


TO-92

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CBO}	75	Vdc
Emitter–Base Voltage	V_{EBO}	6.5	Vdc
Collector Current — Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 10 \text{ }\mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	75	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 60 \text{ Vdc}$, $V_{EB(off)} = 3.0 \text{ Vdc}$)	I_{CEX}	—	10	nAdc
Collector Cutoff Current ($V_{CB} = 60 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 60 \text{ Vdc}$, $I_E = 0$, $T_A = 150^\circ\text{C}$)	I_{CBO}	— —	0.01 10	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	10	nAdc
Collector Cutoff Current ($V_{CE} = 10 \text{ V}$)	I_{CEO}	—	10	nAdc
Base Cutoff Current ($V_{CE} = 60 \text{ Vdc}$, $V_{EB(off)} = 3.0 \text{ Vdc}$)	I_{BEX}	—	20	nAdc

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ($I_C = 0.1\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $T_A = -55^\circ\text{C}$) ($I_C = 150\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ⁽¹⁾ ($I_C = 150\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) ⁽¹⁾ ($I_C = 500\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ⁽¹⁾	h_{FE}	35 50 75 35 100 50 40	— — — — 300 — —	—
Collector–Emitter Saturation Voltage ⁽¹⁾ ($I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$) ($I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$)	$V_{CE(sat)}$	— —	0.3 1.0	Vdc
Base–Emitter Saturation Voltage ⁽¹⁾ ($I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$) ($I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$)	$V_{BE(sat)}$	0.6 —	1.2 2.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

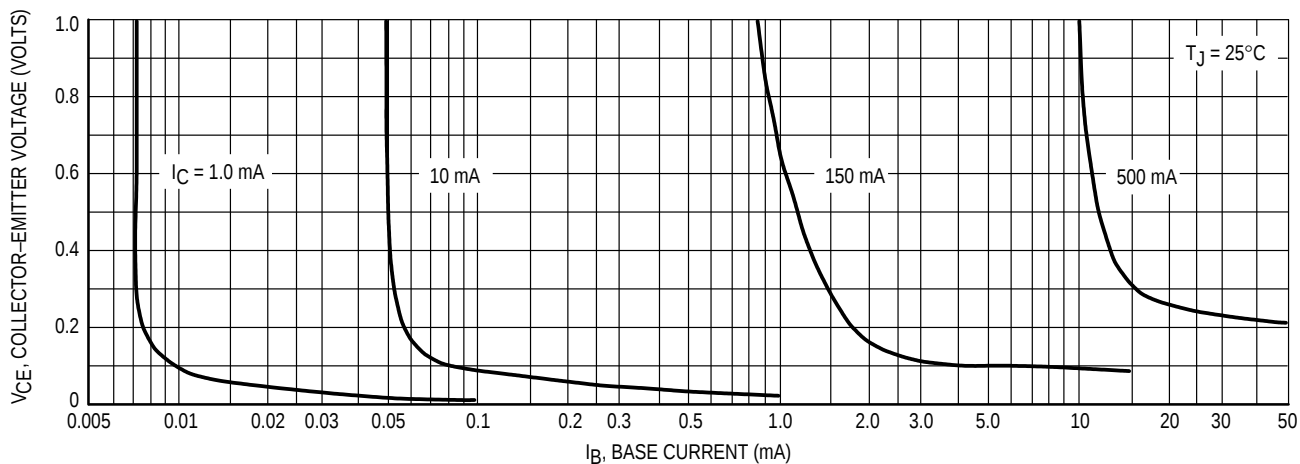
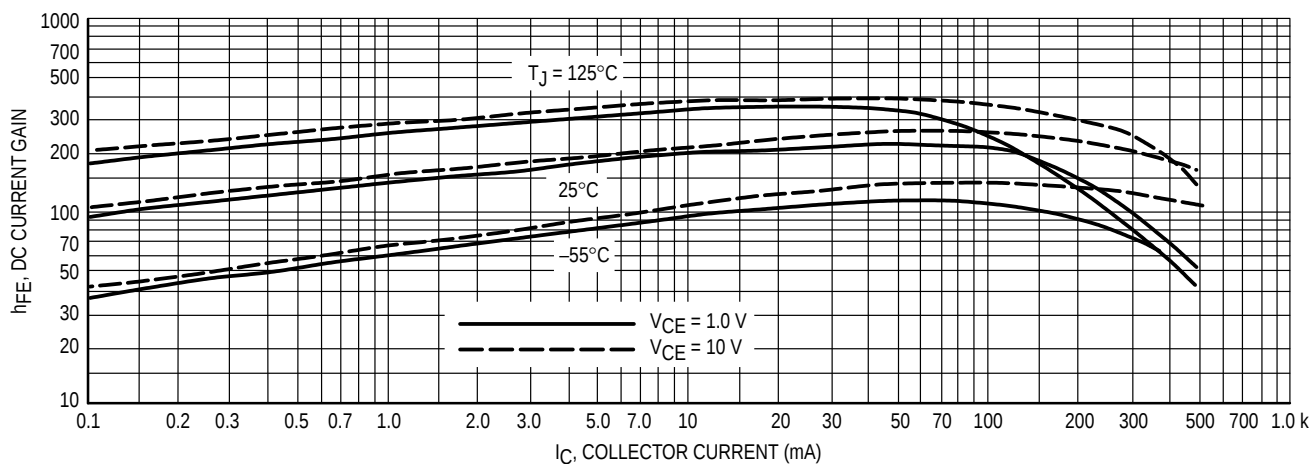
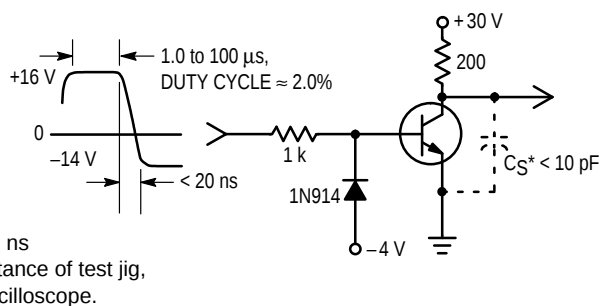
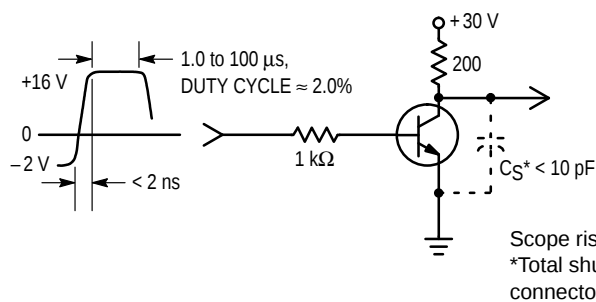
Current–Gain — Bandwidth Product ⁽²⁾ ($I_C = 20\text{ mA}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	300	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	8.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	—	25	pF
Input Impedance ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{ie}	2.0 0.25	8.0 1.25	k Ω
Voltage Feedback Ratio ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{re}	— —	8.0 4.0	$\times 10^{-4}$
Small–Signal Current Gain ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	50 75	300 375	—
Output Admittance ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{oe}	5.0 25	35 200	μmhos
Collector Base Time Constant ($I_E = 20\text{ mA}$, $V_{CB} = 20\text{ Vdc}$, $f = 31.8\text{ MHz}$)	$r_b'C_C$	—	150	ps
Noise Figure ($I_C = 100\text{ }\mu\text{A}$, $V_{CE} = 10\text{ Vdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$)	N_F	—	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = 30 Vdc, V _{BE(off)} = –2.0 Vdc, I _C = 150 mA, I _{B1} = 15 mA) (Figure 1)	t _d	—	10	ns
Rise Time		t _r	—	25	ns
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mA, I _{B1} = I _{B2} = 15 mA) (Figure 2)	t _s	—	225	ns
Fall Time		t _f	—	60	ns

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.
2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS



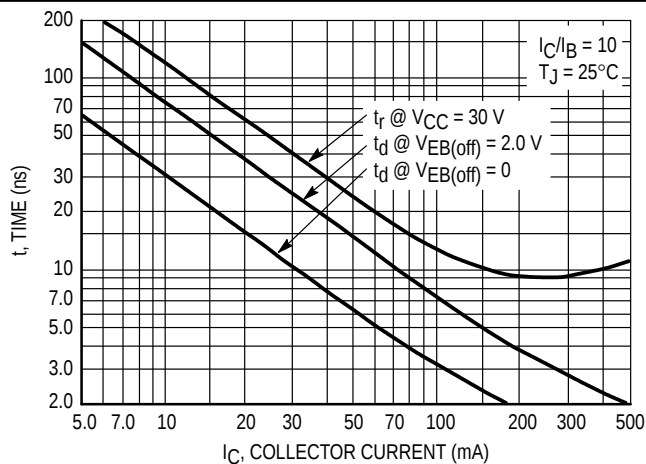


Figure 5. Turn-On Time

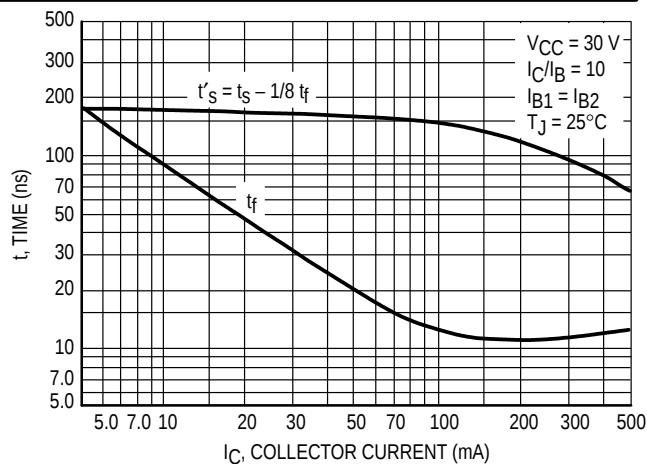


Figure 6. Turn-Off Time

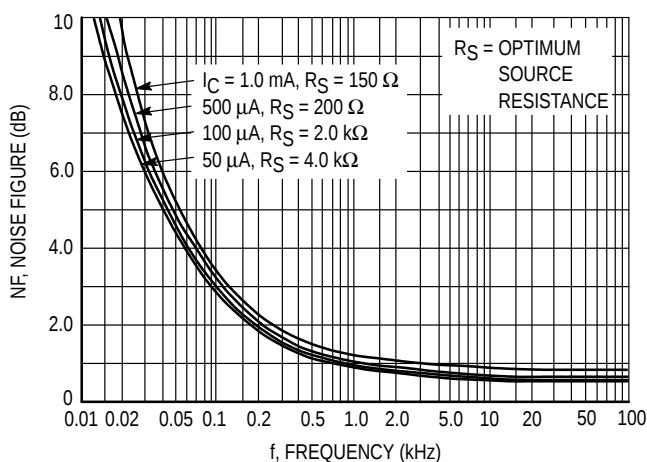


Figure 7. Frequency Effects

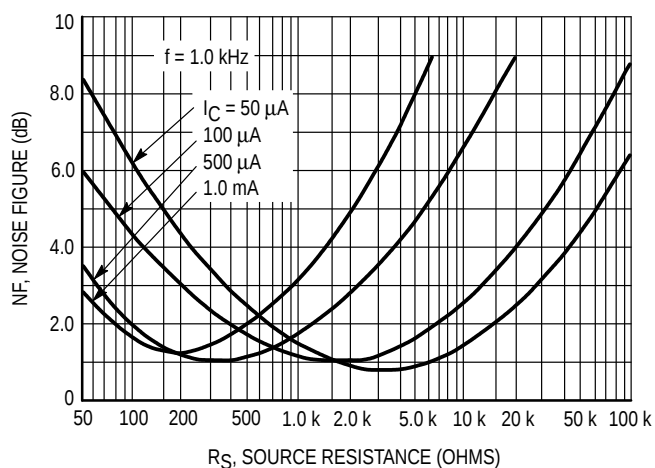


Figure 8. Source Resistance Effects

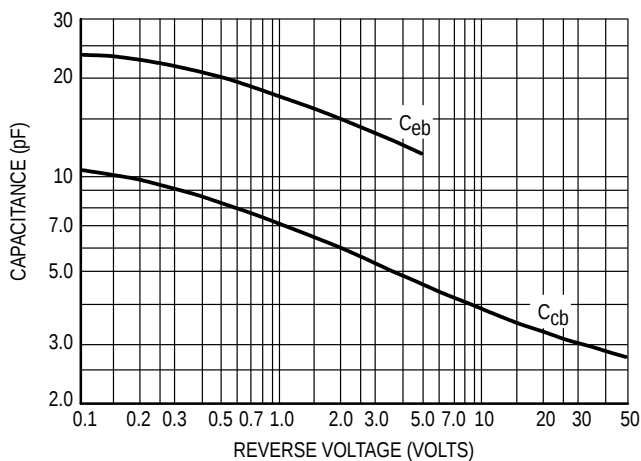


Figure 9. Capacitances

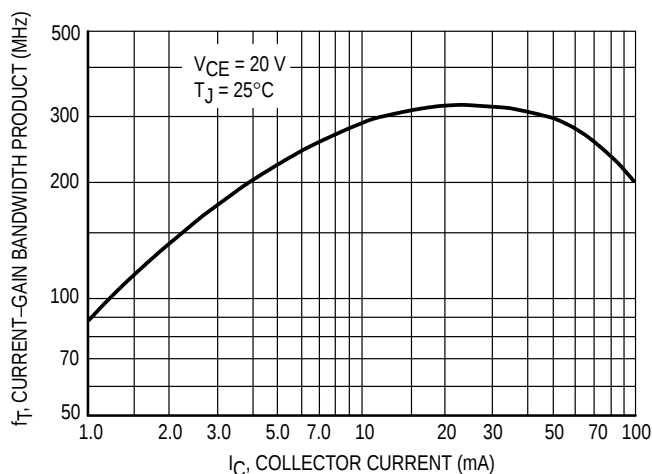


Figure 10. Current-Gain Bandwidth Product

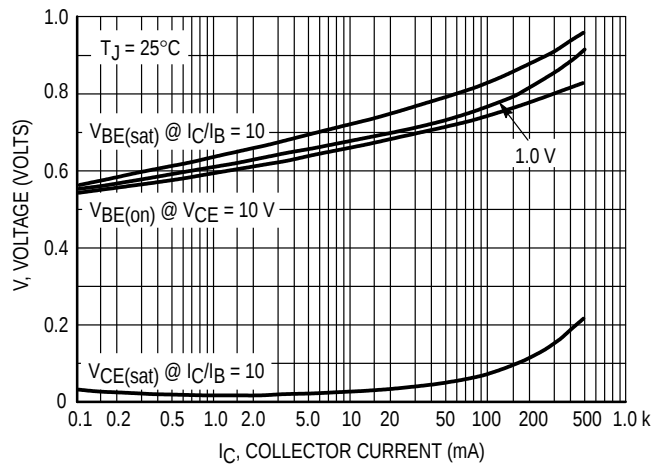


Figure 11. "On" Voltages

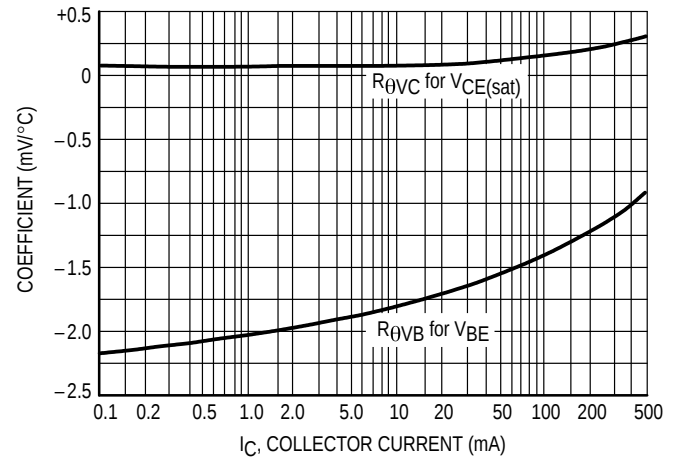


Figure 12. Temperature Coefficients